TOSHIBA MOS DIGITAL INTEGRATED CIRCUIT SILICON GATE CMOS

524,288-WORD BY 8-BIT CMOS STATIC RAM

DESCRIPTION

The TC55V8512JI/FTI is a 4,194,304-bit high-speed static random access memory (SRAM) organized as 524,288 words by 8 bits. Fabricated using CMOS technology and advanced circuit techniques to provide high speed, it operates from a single 3.3 V power supply. Chip enable ($\overline{CE}$) can be used to place the device in a low-power mode, and output enable ($\overline{OE}$) provides fast memory access. This device is well suited to cache memory applications where high-speed access and high-speed storage are required. All inputs and outputs are directly LVTTL compatible. The TC55V8512JI/FTI is available in plastic 36-pin SOJ and 44-pin TSOP with 400mil width for high density surface assembly. The TC55V8512JI/FTI guarantees −40° to 85°C operating temperature so it is suitable for use in wide operating temperature system.

FEATURES

- Fast access time (the following are maximum values)
  TC55V8512JI/FTI-12:12 ns
  TC55V8512JI/FTI-15:15 ns
- Low-power dissipation
  (the following are maximum values)

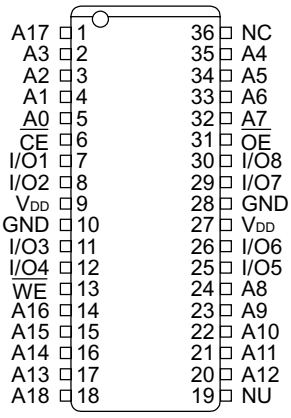
Cycle Time	12	15	20	25	ns
Operation (max)	180	150	140	120	mA

  Standby:10 mA (both devices)

- Single power supply voltage of 3.3 V ± 0.3 V
- Fully static operation
- All inputs and outputs are LVTTL compatible
- Output buffer control using $\overline{OE}$
- Package:
  SOJ36-P-400-1.27 (JI) (Weight: 1.35 g typ)
  TSOP II44-P-400-0.80 (FTI) (Weight: 0.45 g typ)

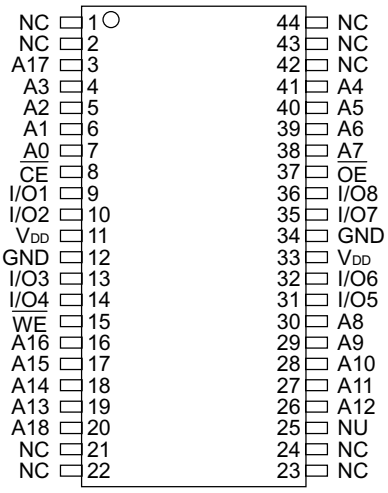
PIN ASSIGNMENT (TOP VIEW)

36 PIN SOJ



(TC55V8512JI)

44 PIN TSOP

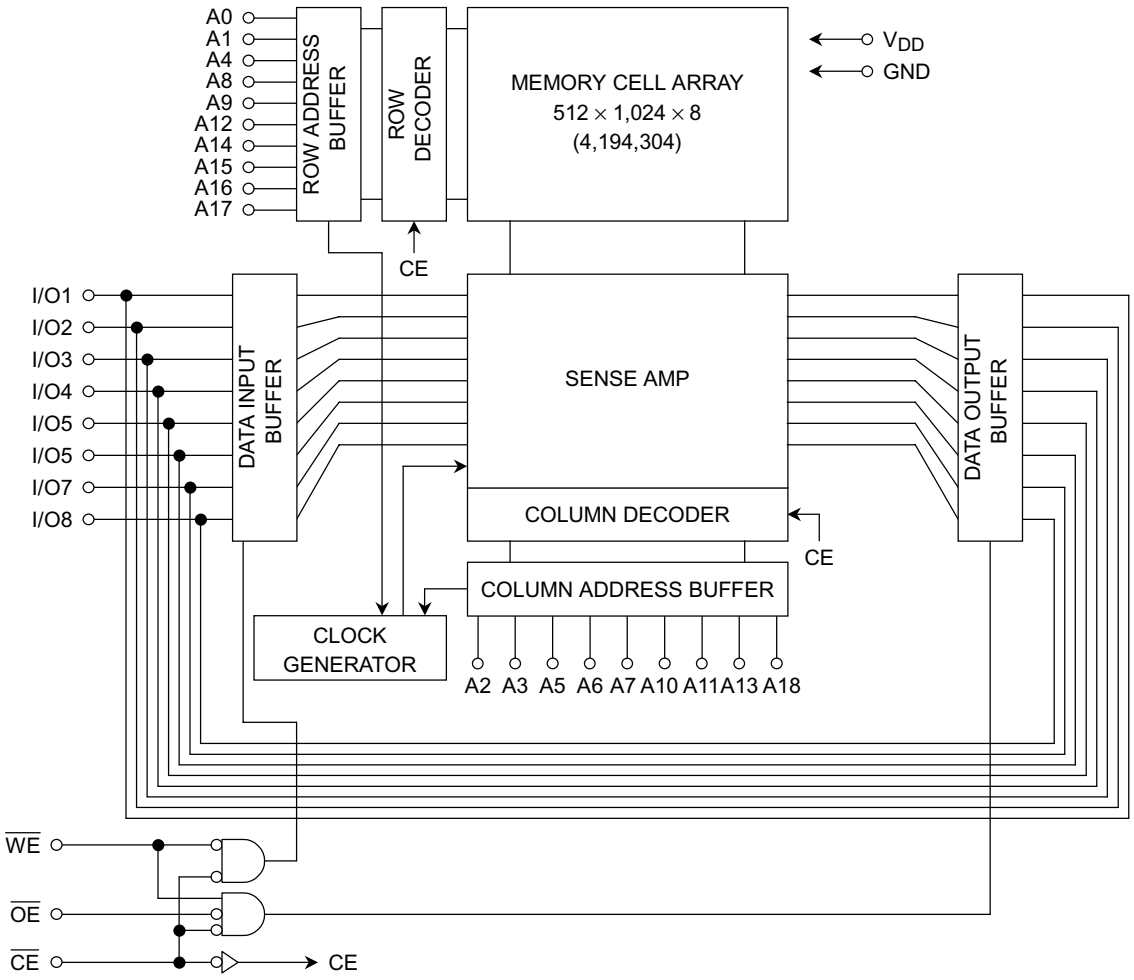


(TC55V8512FTI)

PIN NAMES

A0 to A18	Address Inputs
I/O1 to I/O8	Data Inputs/Outputs
$\overline{CE}$	Chip Enable Input
$\overline{WE}$	Write Enable Input
$\overline{OE}$	Output Enable Input
V_{DD}	Power (+3.3 V)
GND	Ground
NC	No Connection
NU	Not Usable (Input)

BLOCK DIAGRAM



MAXIMUM RATINGS

SYMBOL	RATING	VALUE	UNIT
V_{DD}	Power Supply Voltage	−0.5 to 4.6	V
V_{IN}	Input Terminal Voltage	−0.5* to 4.6	V
$V_{I/O}$	Input/Output Terminal Voltage	−0.5* to V_{DD} + 0.5**	V
P_D	Power Dissipation	1.4	W
T_{solder}	Soldering Temperature (10s)	260	°C
T_{stg}	Storage Temperature	−65 to 150	°C
T_{opr}	Operating Temperature	−40 to 100	°C

*: −1.5 V with a pulse width of 20%・t_{RC} min (4 ns max)
**: V_{DD} + 1.5 V with a pulse width of 20%・t_{RC} min (4 ns max)

DC RECOMMENDED OPERATING CONDITIONS (Ta = −40° to 85°C)

SYMBOL	PARAMETER	MIN	TYP	MAX	UNIT
V_{DD}	Power Supply Voltage	3.0	3.3	3.6	V
V_{IH}	Input High Voltage	2.0	—	V_{DD} + 0.3**	V
V_{IL}	Input Low Voltage	−0.3*	—	0.8	V

*: −1.0 V with a pulse width of 20%・t_{RC} min (4 ns max)
**: V_{DD} + 1.0 V with a pulse width of 20%・t_{RC} min (4 ns max)

DC CHARACTERISTICS (Ta = –40° to 85°C, V_{DD} = 3.3 V ± 0.3 V)

SYMBOL	PARAMETER	TEST CONDITION		MIN	TYP	MAX	UNIT
I_{IL}	Input Leakage Current (Except NU pin)	V_{IN} = 0 to V_{DD}		–1	—	1	μA
I_{LO}	Output Leakage Current	$\overline{CE}$ = V_{IH} or $\overline{WE}$ = V_{IL} or $\overline{OE}$ = V_{IH}, V_{OUT} = 0 to V_{DD}		–1	—	1	μA
$I_{I\ (NU)}$	Input Current (NU pin)	V_{IN} = 0 to 0.8 V		–1	—	20	μA
		V_{IN} = 0 to 0.2 V		–1	—	1	
V_{OH}	Output High Voltage	I_{OH} = –2 mA		2.4	—	—	V
		I_{OH} = –100 μA		V_{DD} – 0.2	—	—	
V_{OL}	Output Low Voltage	I_{OL} = 2 mA		—	—	0.4	
		I_{OL} = 100 μA		—	—	0.2	
I_{DDO}	Operating Current	$\overline{CE}$ = V_{IL}, I_{OUT} = 0 mA, $\overline{OE}$ = V_{IH}, Other Input = V_{IH}/V_{IL}	t_{cycle} = 12 ns	—	—	180	mA
			t_{cycle} = 15 ns	—	—	150	
			t_{cycle} = 20 ns	—	—	140	
			t_{cycle} = 25 ns	—	—	120	
I_{DDS1}	Standby Current	$\overline{CE}$ = V_{IH}, Other Input = V_{IH} or V_{IL}		—	—	55	mA
I_{DDS2}		$\overline{CE}$ = V_{DD} – 0.2 V, Other Input = V_{DD} – 0.2 V or 0.2 V		—	—	10	

CAPACITANCE (Ta = 25°C, f = 1 .0 MHz)

SYMBOL	PARAMETER	TEST CONDITION	MAX	UNIT
C_{IN}	Input Capacitance	V_{IN} = GND	6	pF
$C_{I/O}$	Input/Output Capacitance	$V_{I/O}$ = GND	8	pF

Note: This parameter is periodically sampled and is not 100% tested.

OPERATING MODE

MODE	$\overline{CE}$	$\overline{OE}$	$\overline{WE}$	I/O1 to I/O8	POWER
Read	L	L	H	Output	I_{DDO}
Write	L	*	L	Input	I_{DDO}
Outputs Disable	L	H	H	High Impedance	I_{DDO}
Standby	H	*	*	High Impedance	I_{DDS}

* : Don't care

Note: The NU pin must be left unconnected or tied to GND or a voltage level of less than 0.8 V.
You must not apply a voltage of more than 0.8 V to the NU.

AC CHARACTERISTICS (Ta = –40° to 85°C (See Note 1), V_{DD} = 3.3 V ± 0.3 V)

READ CYCLE

SYMBOL	PARAMETER	TC55V8512JI/FTI				UNIT
		-12		-15		
		MIN	MAX	MIN	MAX	
t_{RC}	Read Cycle Time	12	—	15	—	ns
t_{ACC}	Address Access Time	—	12	—	15	
t_{CO}	Chip Enable Access Time	—	12	—	15	
t_{OE}	Output Enable Access Time	—	6	—	8	
t_{OH}	Output Data Hold Time from Address Change	3	—	4	—	
t_{COE}	Output Enable Time from Chip Enable	3	—	4	—	
t_{OEE}	Output Enable Time from Output Enable	1	—	1	—	
t_{COD}	Output Disable Time from Chip Enable	—	7	—	8	
t_{ODO}	Output Disable Time from Output Enable	—	7	—	8	

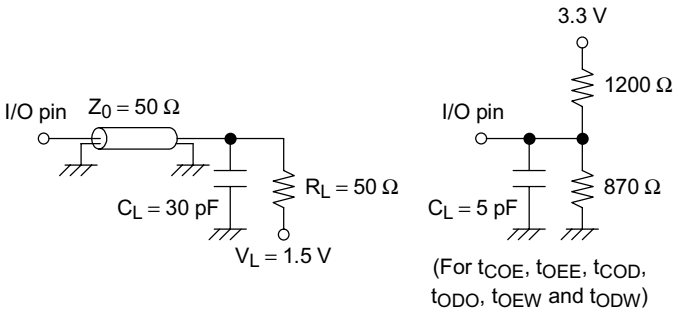
WRITE CYCLE

SYMBOL	PARAMETER	TC55V8512JI/FTI				UNIT
		-12		-15		
		MIN	MAX	MIN	MAX	
t_{WC}	Write Cycle Time	12	—	15	—	ns
t_{WP}	Write Pulse Width	8	—	9	—	
t_{CW}	Chip Enable to End of Write	10	—	12	—	
t_{AW}	Address Valid to End of Write	10	—	12	—	
t_{AS}	Address Setup Time	0	—	0	—	
t_{WR}	Write Recovery Time	0	—	0	—	
t_{DS}	Data Setup Time	7	—	8	—	
t_{DH}	Data Hold Time	0	—	0	—	
t_{OEW}	Output Enable Time from Write Enable	1	—	1	—	
t_{ODW}	Output Disable Time from Write Enable	—	7	—	8	

AC TEST CONDITIONS

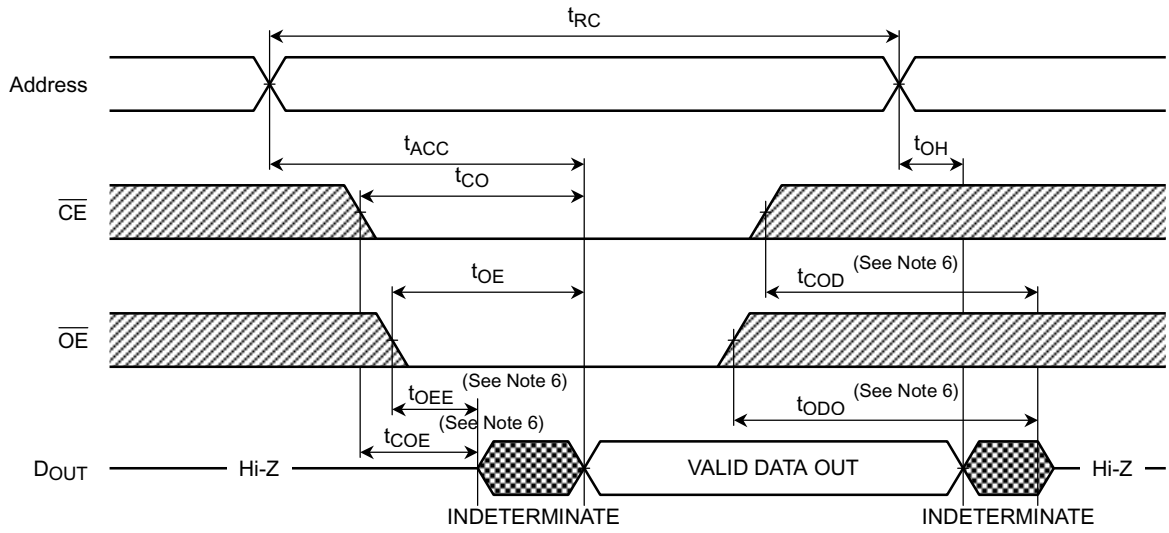
PARAMETER	TEST CONDITION
Input Pulse Level	3.0 V/ 0.0 V
Input Pulse Rise and Fall Time	2 ns
Input Timing Measurement Reference Level	1.5 V
Output Timing Measurement Reference Level	1.5 V
Output Load	Fig.1

Fig.1

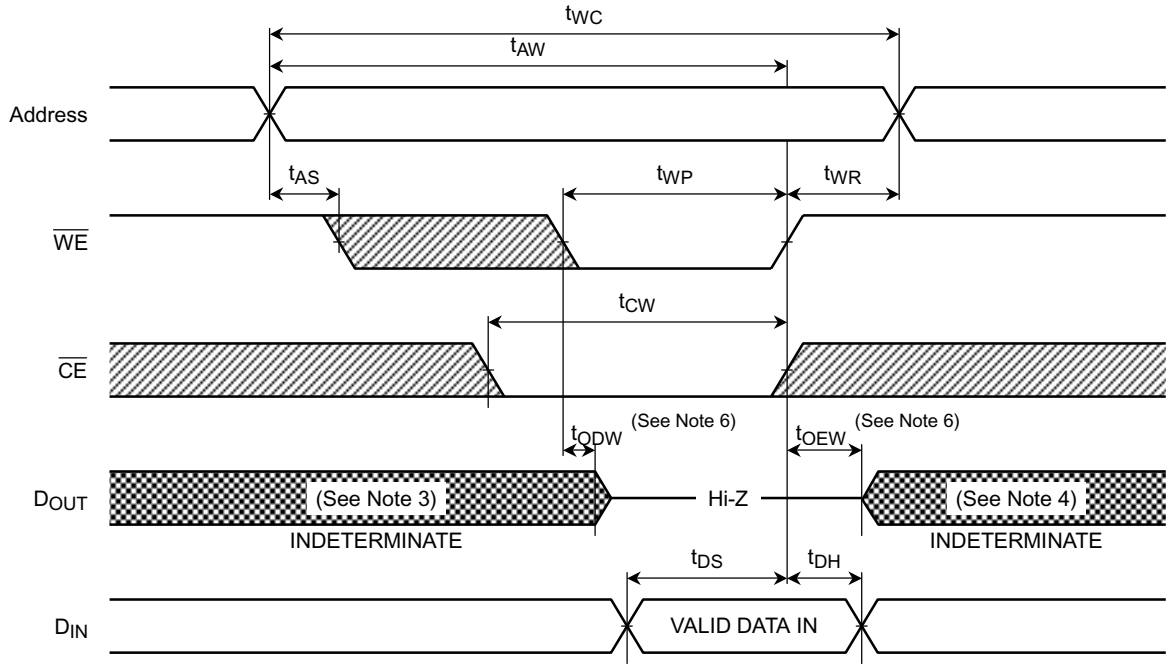


TIMING DIAGRAMS

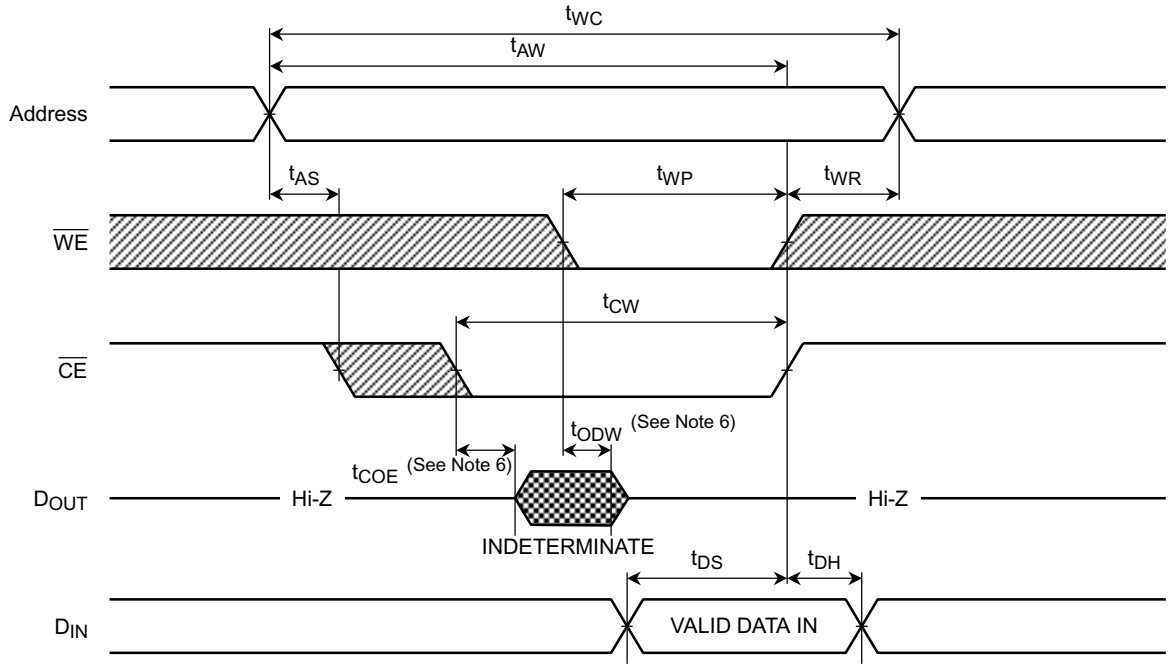
READ CYCLE (See Note 2)



WRITE CYCLE 1 ($\overline{WE}$ CONTROLLED) (See Note 5)



WRITE CYCLE 2 ($\overline{CE}$ CONTROLLED) (See Note 5)



Note:

(1) Operating temperature (Ta) is guaranteed for transverse air flow exceeding 400 linear feet per minute.

(2) $\overline{WE}$ remains HIGH for the Read Cycle.

(3) If $\overline{CE}$ goes LOW coincident with or after $\overline{WE}$ goes LOW, the outputs will remain at high impedance.

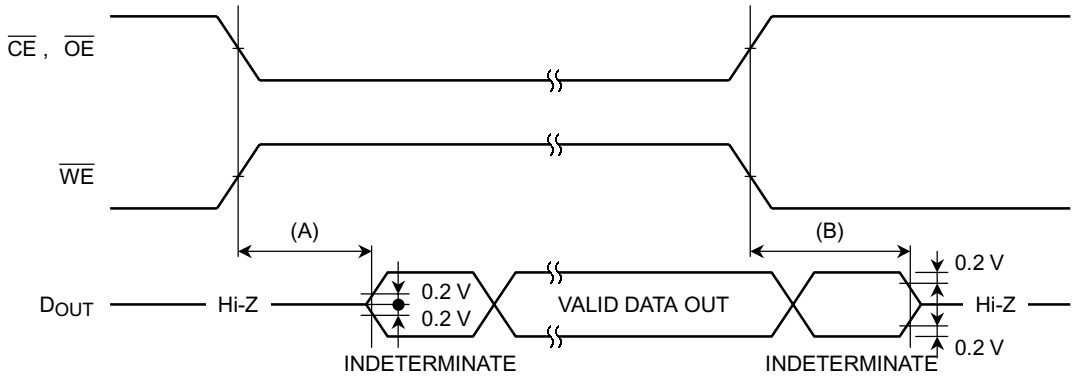
(4) If $\overline{CE}$ goes HIGH coincident with or before $\overline{WE}$ goes HIGH, the outputs will remain at high impedance.

(5) If $\overline{OE}$ is HIGH during the write cycle, the outputs will remain at high impedance.

(6) The parameters specified below are measured using the load shown in Fig.1.

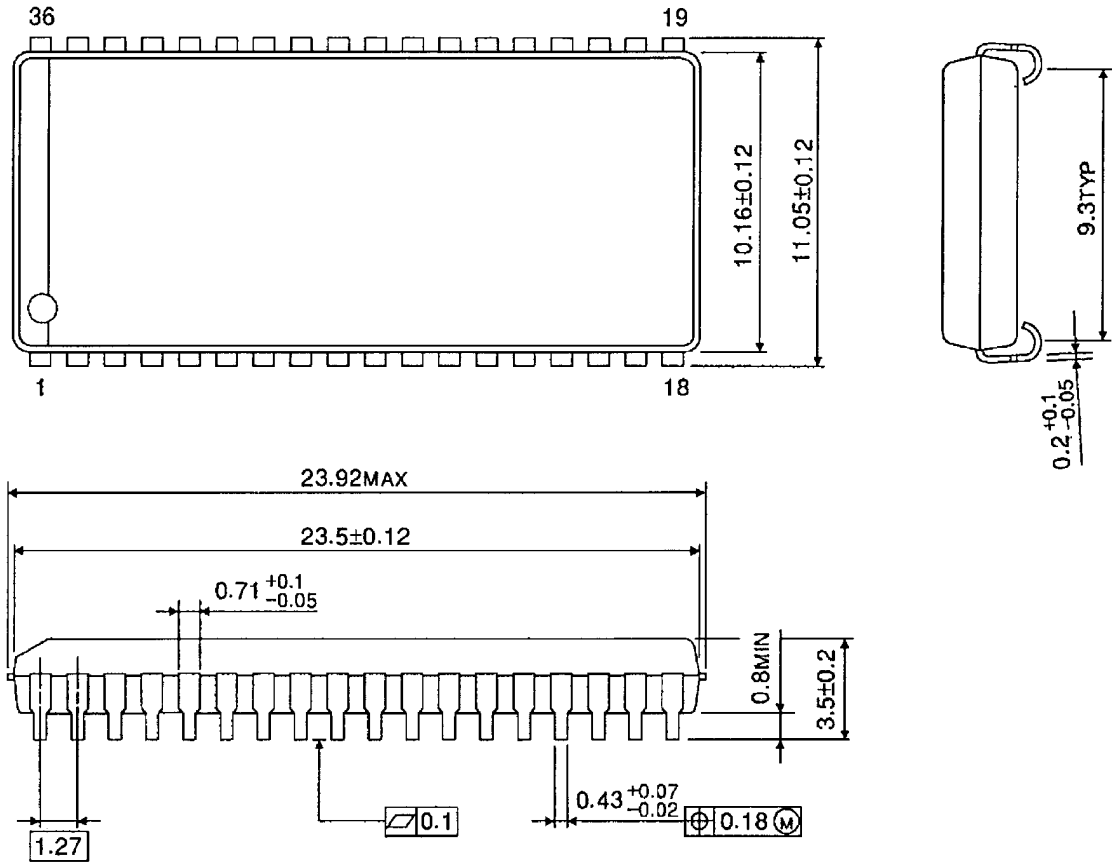
(A) t_{COE}, t_{OEE}, t_{OEW} ····· Output Enable Time

(B) t_{COD}, t_{ODO}, t_{ODW} ····· Output Disable Time



PACKAGE DIMENSIONS

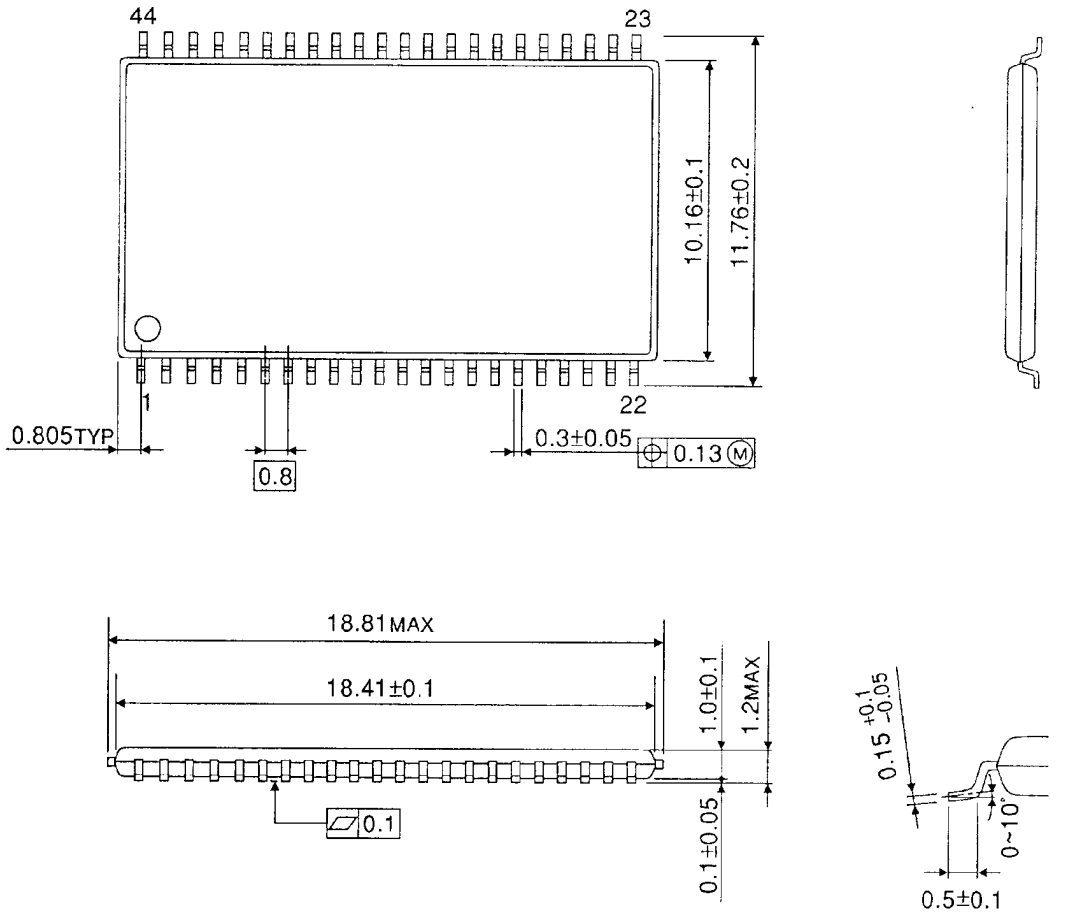
SOJ36-P-400-1.27 Unit : mm



Weight: 1.35 g (typ)

PACKAGE DIMENSIONS

TSOP II 44-P-400-0.80 Unit : mm



Weight: 0.45 g (typ)

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